



SEMICONDUCTOR PACKAGE HAVING GROOVES FORMED AT SIDE
FLASH, GROOVE FORMING METHOD, AND DEFLASHING METHOD USING
SEMICONDUCTOR PACKAGE FORMED WITH GROOVES

Disclosed herein is a deflash technique for removing flash from a portion of a semiconductor package to be plated before a plating process and after a sealing process accompanied by resin molding during the manufacture of semiconductors, and more particularly a semiconductor package having grooves formed at side flash, a groove forming method, and a deflshing method using the semiconductor package, for removing the side flash formed at a side portion of a lead frame where it is difficult to perform a deflashing process. Conventionally, it is impossible to completely remove side flash remaining on the lead frame at a region where it is difficult to perform a deflashing process even by injecting water jet or media at a very high pressure, or by irradiating laser beams thereto while changing irradiation directions. However, according to the present invention, by virtue of the grooves formed at the side flash by laser irradiation, it is possible to easily remove the side flash and to improve deflashing efficiency and quality of products.

Figure 4



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